

Pyroelectric Response in Thin Ferroelectric (Hf,Zr)O₂

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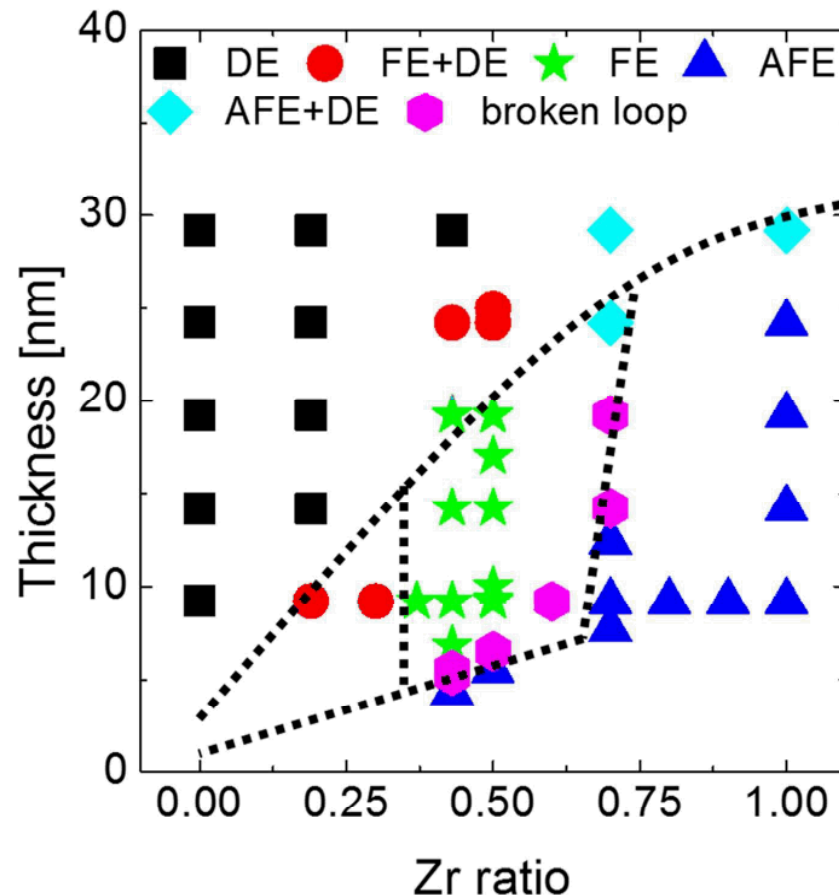
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Ferroelectric HfO₂

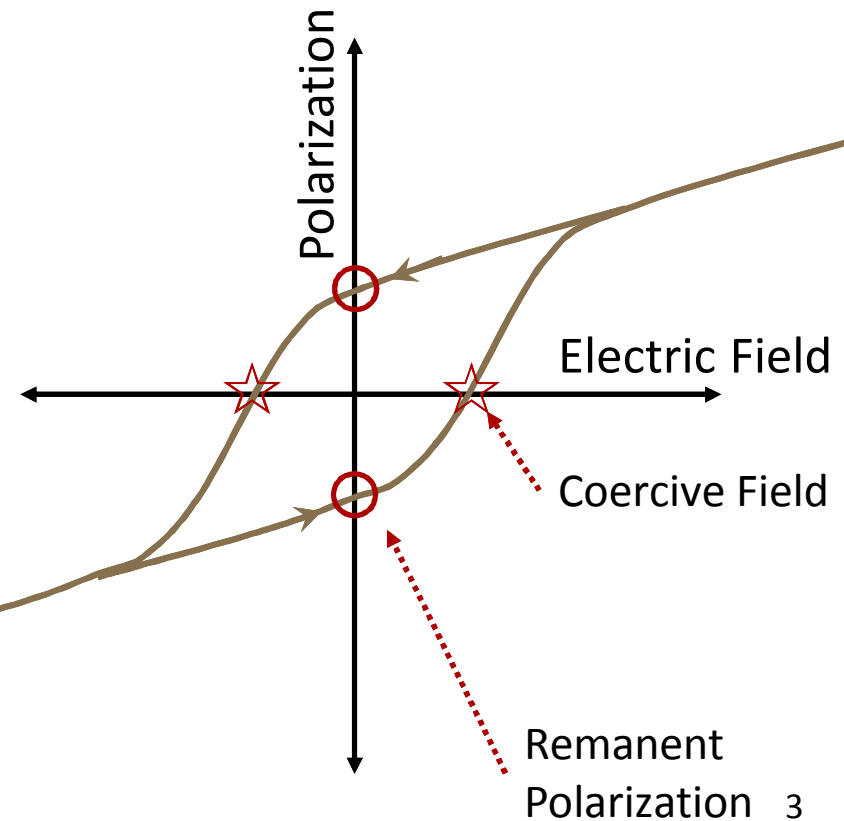
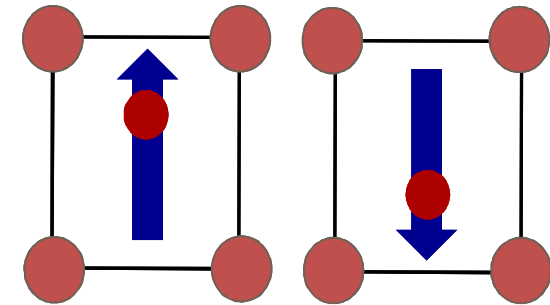
- 2011 Boscke *et al.* – Namlab
 - 2 to 5% Si:HfO₂ via ALD with TiN top and bottom electrodes and anneal.
 - Proposed metastable orthorhombic crystal structure.
- Since then:
 - Dopants: Zr, Gd, Al, none,...
 - Electrodes: Mostly TiN, TaN, Pt, Ir, Ru Si, ...
 - Thickness: 25 to ~5 nm, maybe less
- CMOS compatible ferroelectric stable at <20 nm thickness.
 - Applications: ferroelectric memory, energy storage & harvesting, low power FETs.



DE-dielectric
FE-ferroelectric
AFE-antiferroelectric-like

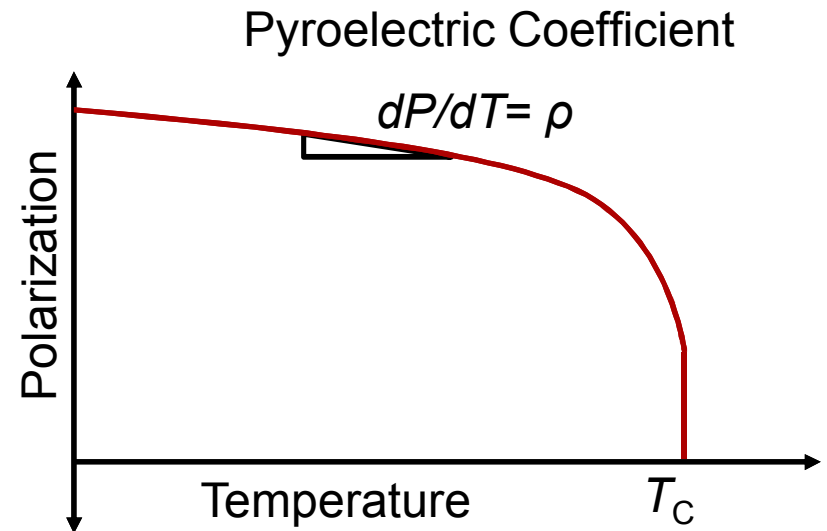
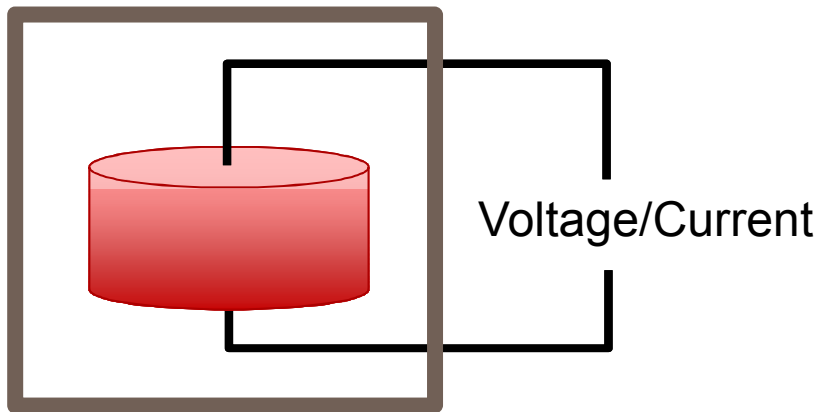
What is a Ferroelectric Material?

- Spontaneous polarization which can be reoriented by an electric field
- Noncentrosymmetric ionic crystals
 - Centers of positive and negative charge do not coincide
- Applications
 - Memory: FRAM
 - Actuators: Ultrasound, Sonar, AFMs
 - Capacitors: Cellphones and nearly all electronics
 - Sensors: Night vision, IR cameras
 - Due to pyroelectric effect



What is the Pyroelectric Effect?

- If: Spontaneous polarization
- Then: Uniform change in temperature creates a change in polarization
 - Change in polarization can be measured as a voltage or current.



Pyroelectric Measurements

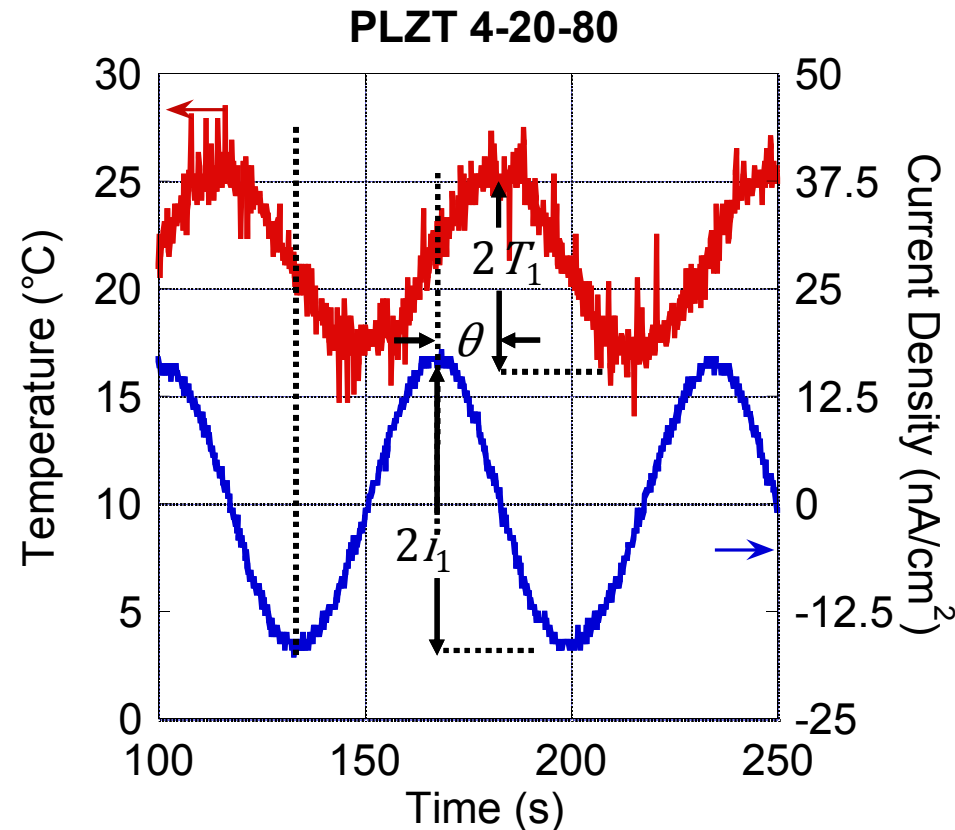
- Dynamic & Direct Measurement
 - Continuous change in temp and measure the current simultaneously
 - Sinusoidal Oscillating Temperature
 - Pyroelectric current depends on change in temperature with time

$$i_1 \sin(\theta) = pA\omega T_1$$

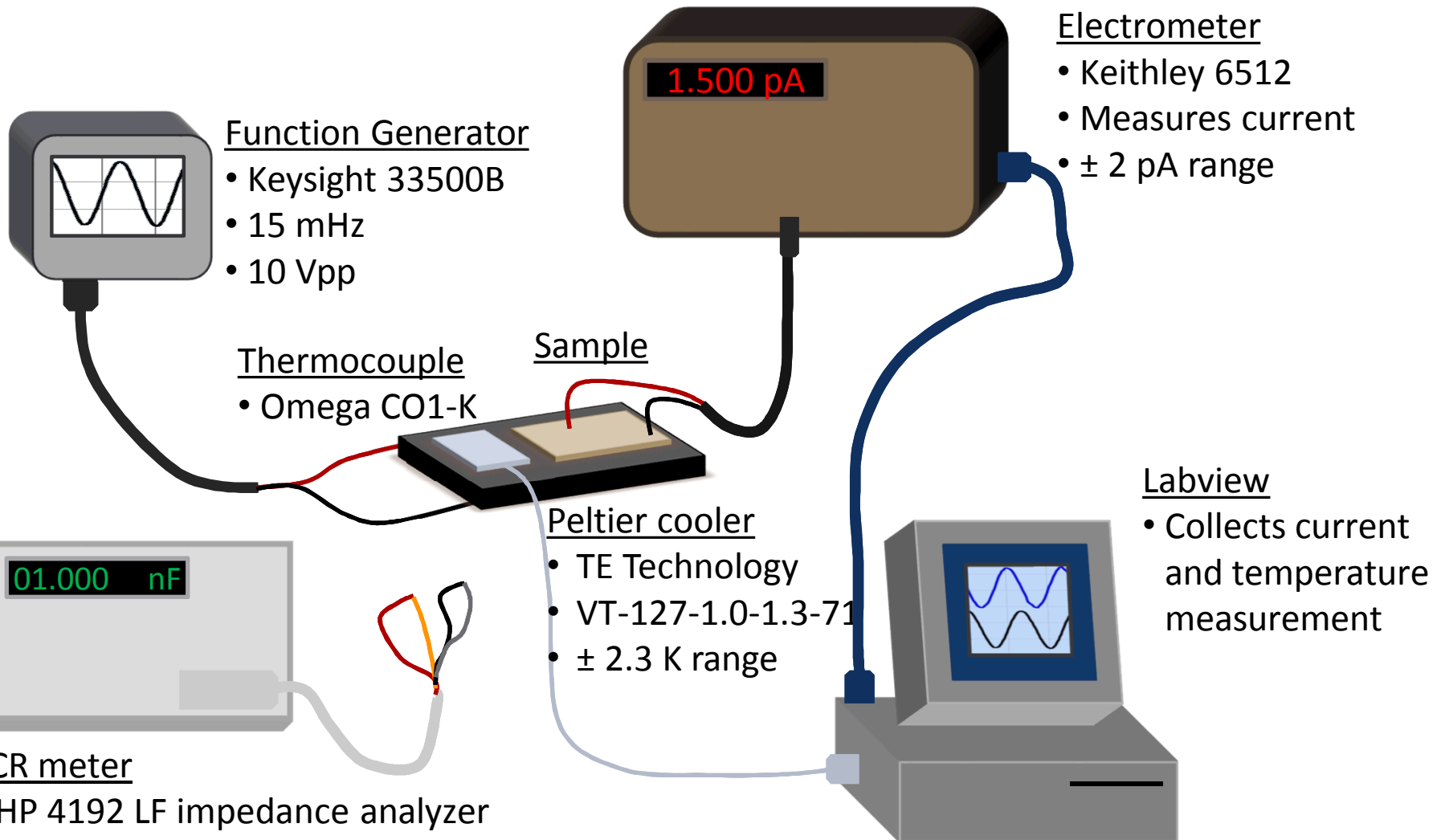
p – pyroelectric coefficient

ω – angular frequency of temperature

A – area of device

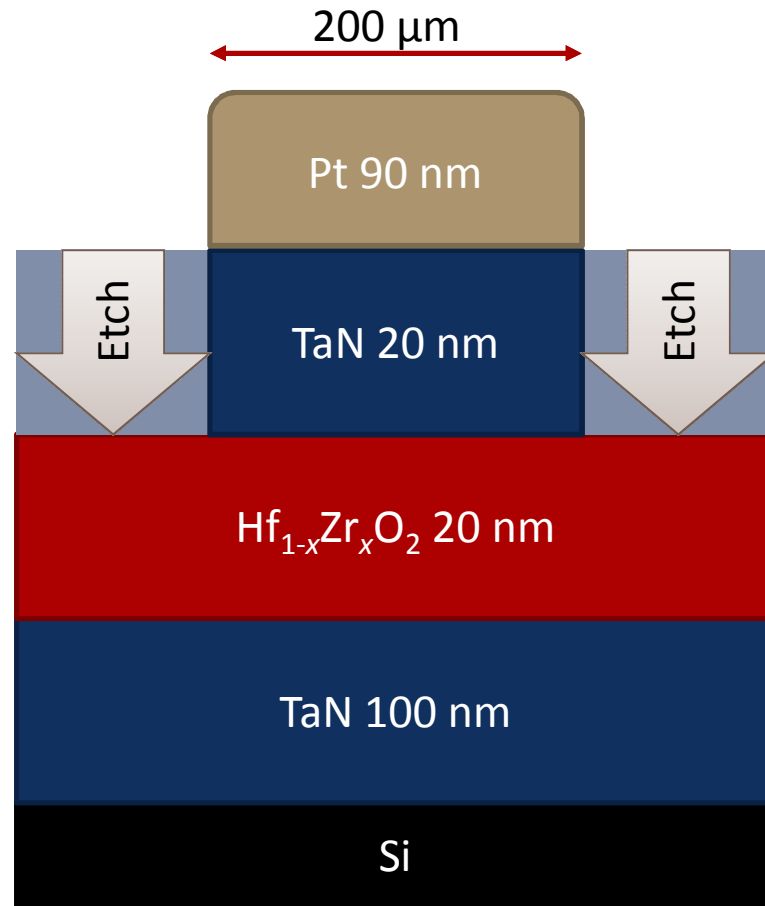


Pyroelectric Setup

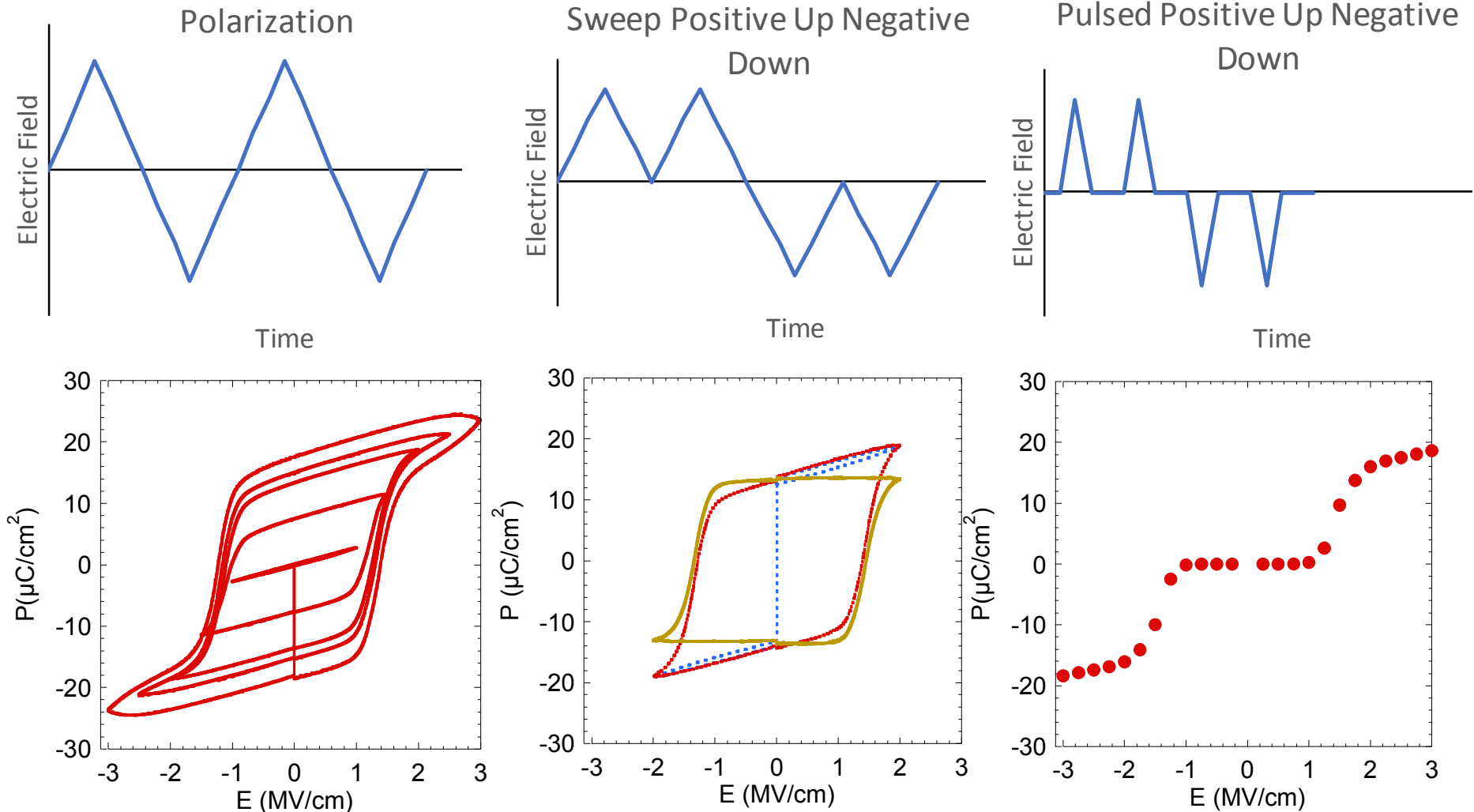


Experimental and Device Stack

- RF sputter TaN from TaN target
- Thermal ALD $\text{Hf}_{1-x}\text{Zr}_x\text{O}_2$ at 150 °C by TDMA Hf, TDMA Zr, and H_2O
 - HfO_2 1.01 nm GPC
 - ZrO_2 0.99 nm GPC
 - 5 cycle ZrO_2 & 5 cycle HfO_2 supercycle (~1 nm)
- Rapid thermal anneal 30s at 600 °C under nitrogen
- Sputter Pt through shadow-mask
- ICP reactive ion etch
 - SF_6 and C_4F_8 atmosphere



Polarization: Test Profiles

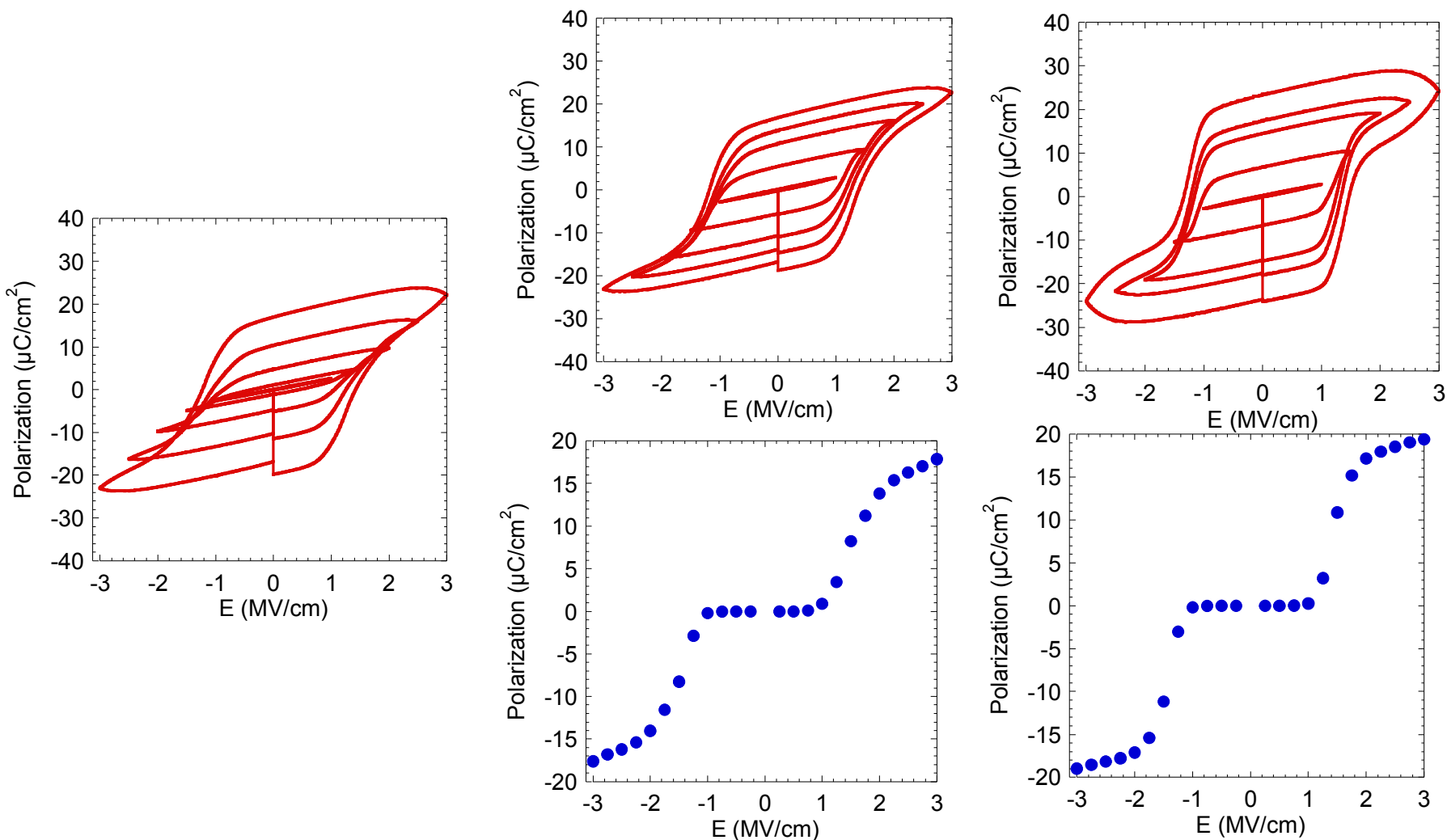


Polarization: Wake Up

20 nm Initial

6 V Polarization

4 V Square Wave 10^3 cycles

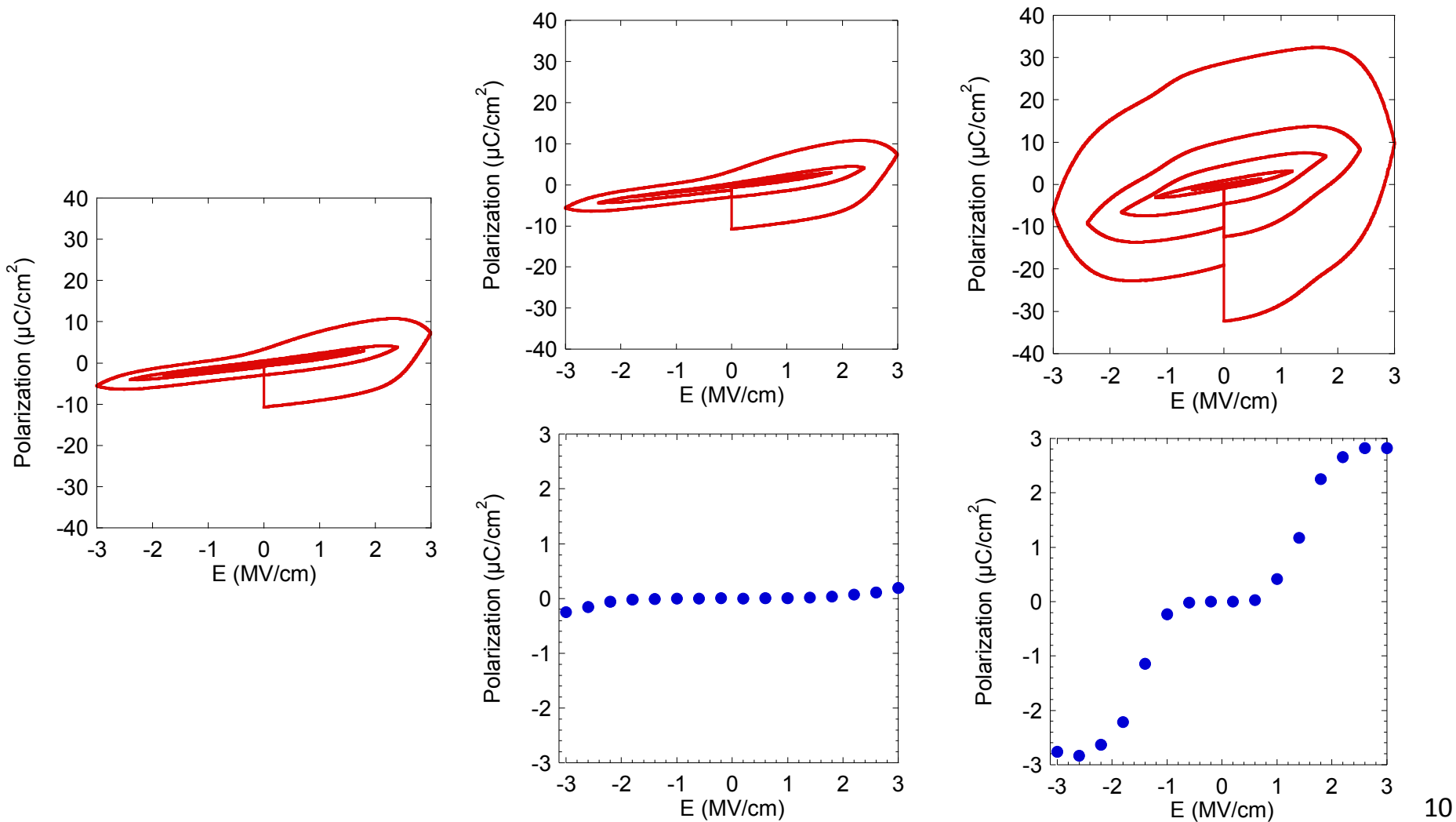


Polarization: Wake Up

5 nm Initial

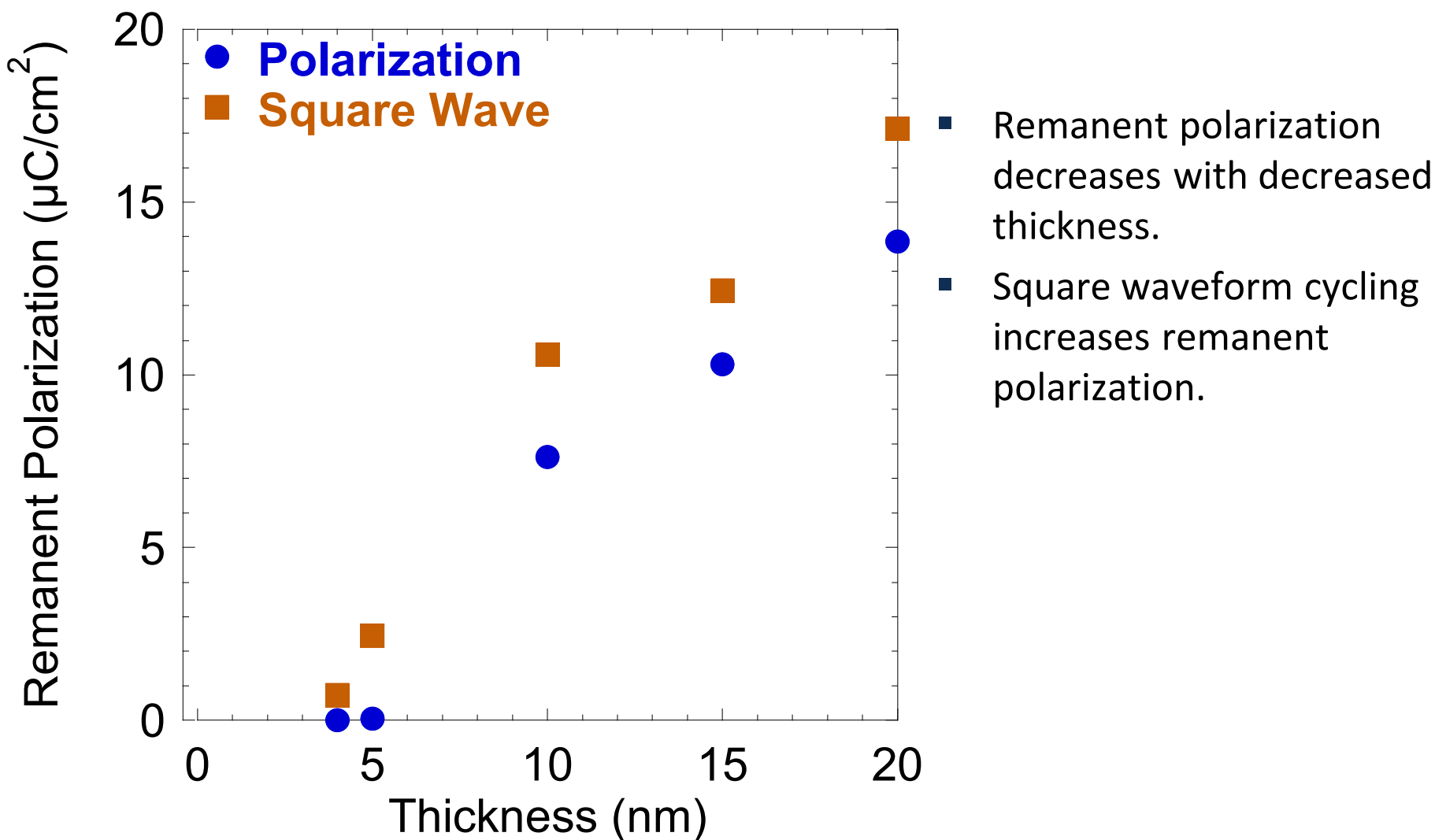
1.5 V Polarization

1.5 V Square Wave 10^5 cycles

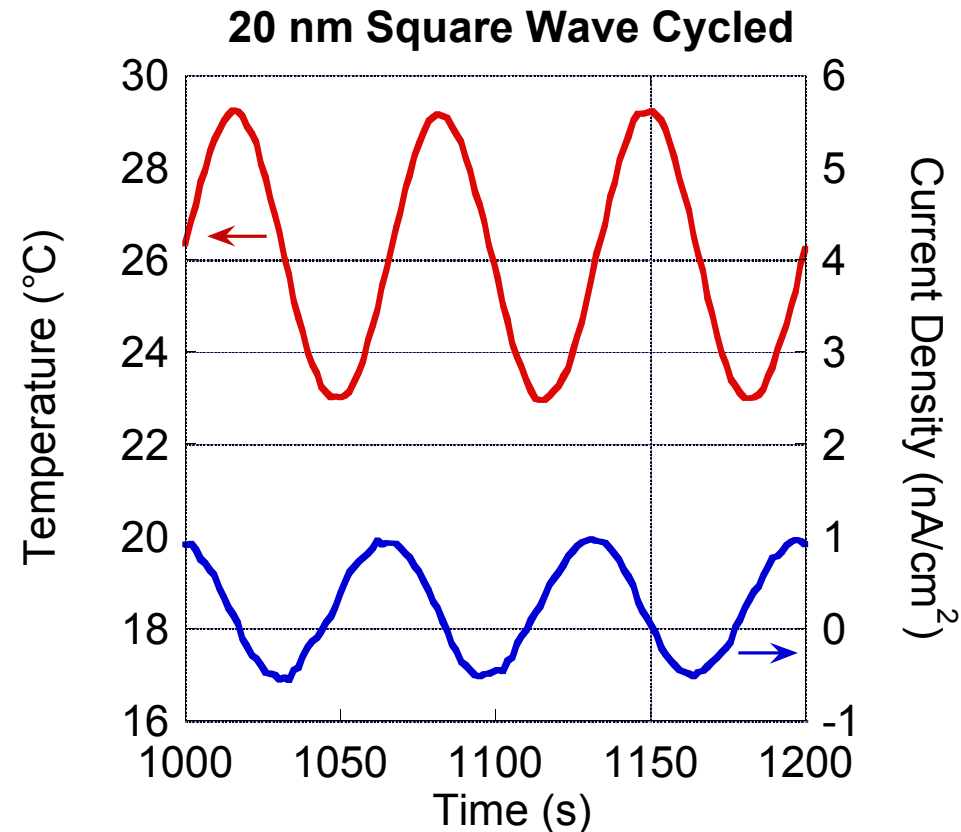
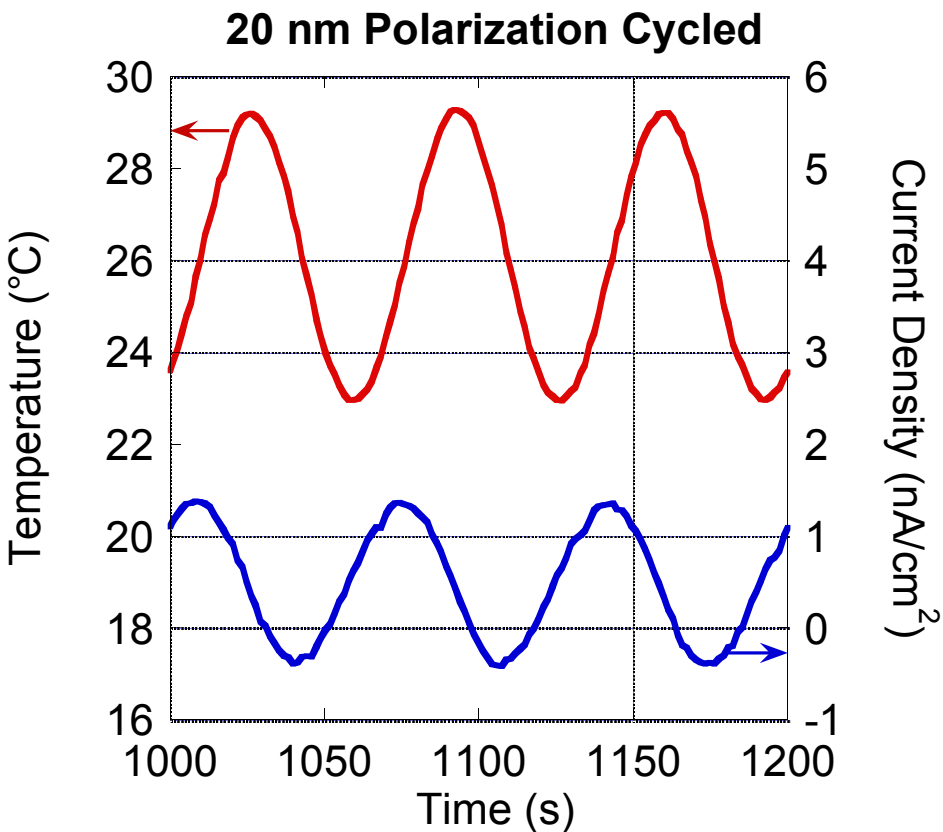


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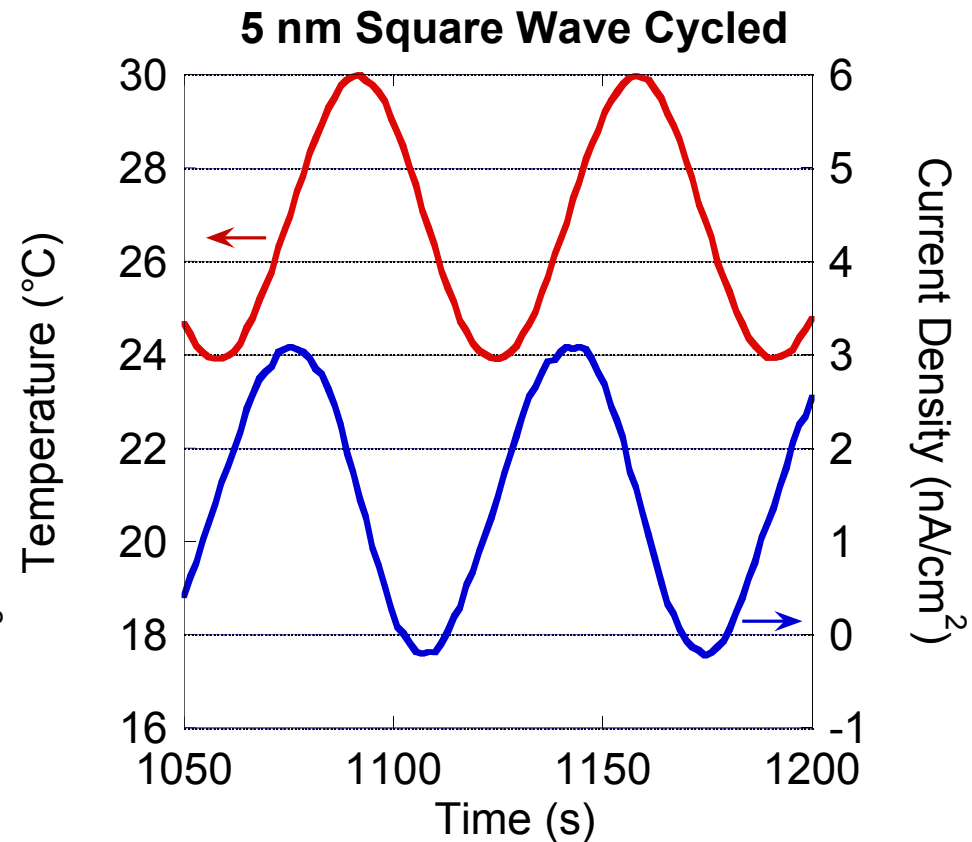
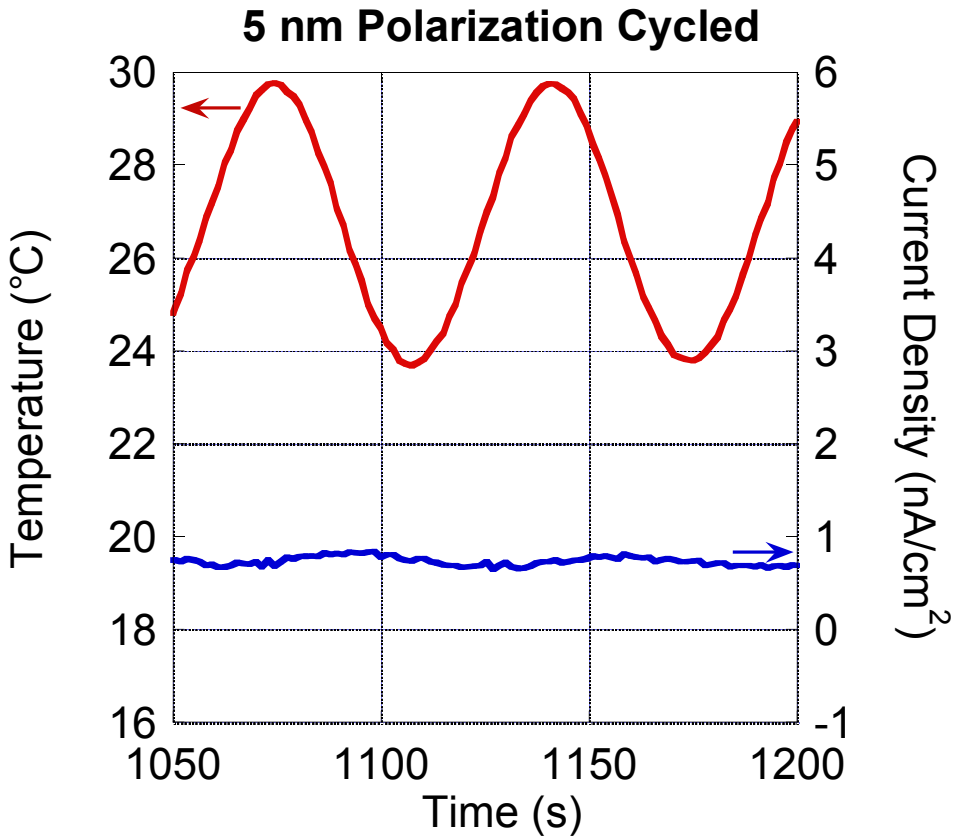
Polarization Trend



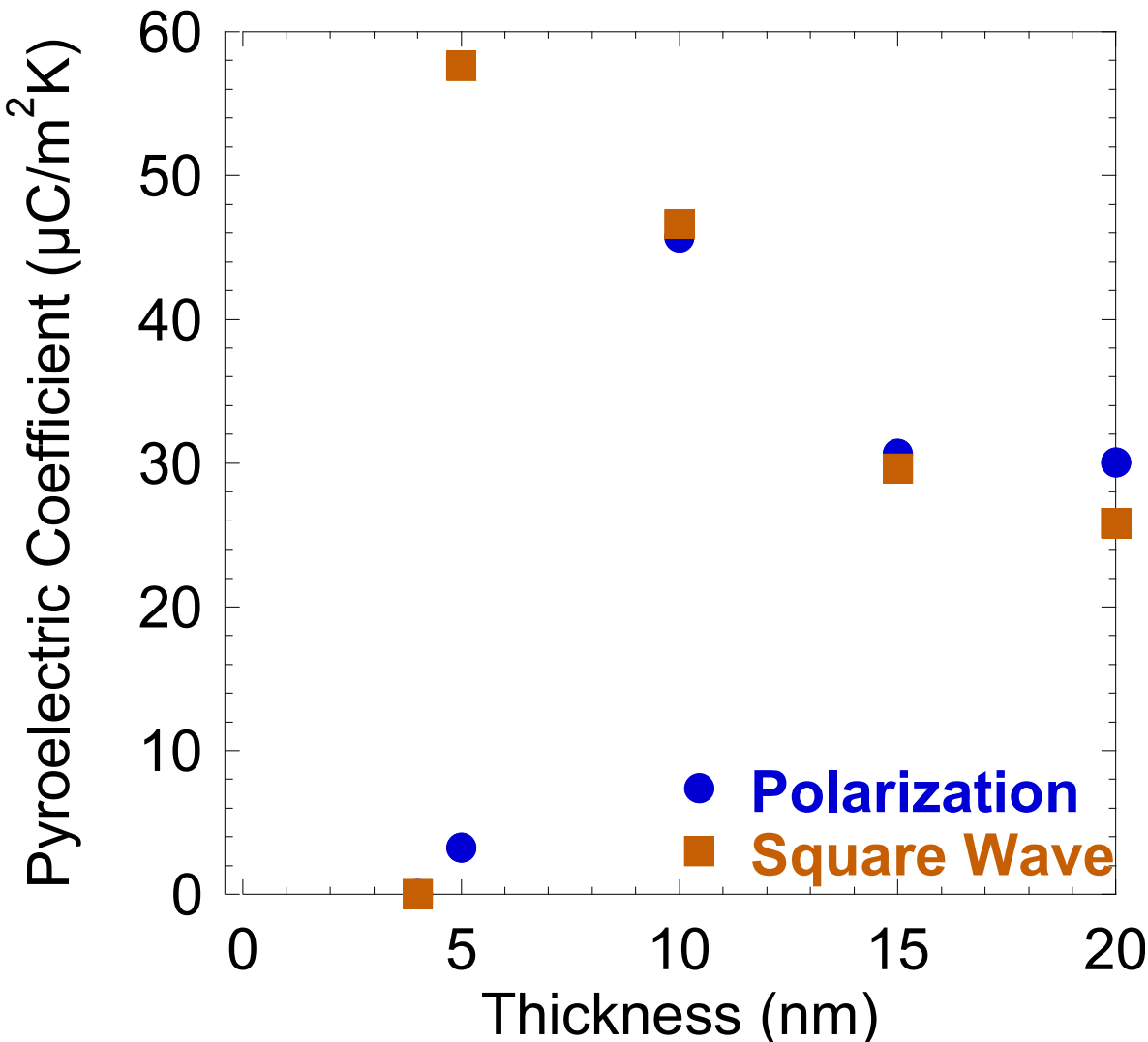
Pyroelectric Measurement Data



Pyroelectric Measurement Data

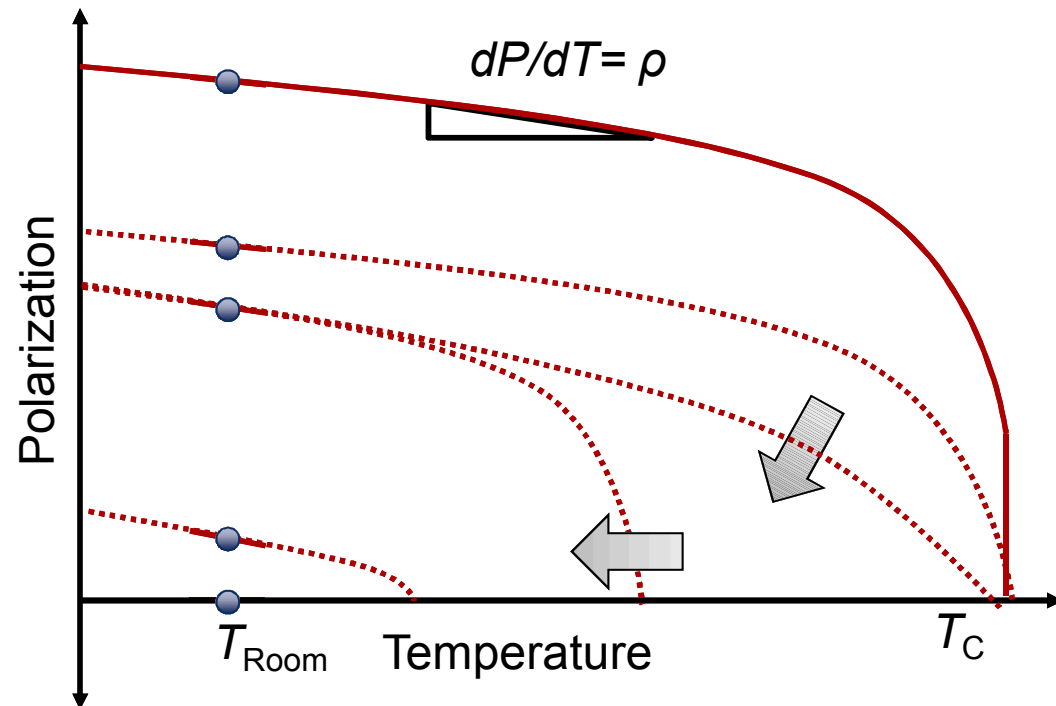


Pyroelectric Coefficient



- Pyroelectric coefficient increases as thickness decreases.
- Wake up makes little difference.
 - Except 5 nm.

Pyroelectric Coefficient & Polarization



- As thickness decreases:
 - Polarization decreases.
 - Pyroelectric coefficient increases.
- Polarization vs. temperature curve response:
 - T_C decreases.
 - Phase transition becomes more gradual.

Conclusions

- ALD (Hf, Zr)O₂ displays switchable polarization and pyroelectric response down to 5 nm.
 - Polarization decreases with decreased thickness.
 - Pyroelectric response increased with decreased thickness.
- Pyroelectric measurements provide insight into stability of ferroelectric orthorhombic phase: Curie temperature and transition.